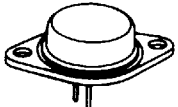




# Power MOSFETS

ECG Type	Description and Application	Transconductance gfs $\mu$ mhos	Drain to Source Breakdown Voltage BV <sub>DSS</sub>	Gate to Source Breakdown Voltage BV <sub>GS</sub>	Continuous Drain Current I <sub>D</sub> Amps	Gate to Source Threshold Voltage V <sub>GS</sub> (th)	Drain to Source Resistance r <sub>DS</sub> (on) Ohms	Input Cap C <sub>iss</sub> pf	Device Dissipation @T <sub>C</sub> =25° C P <sub>D</sub> Watts	Package
										Case/Fig./Basing
ECG2392 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	100 Min	±20 Max*	32	4 Max	.06 Max	1500 Max	125 Max	TO-3 Fig. T28   ECG2392 use Fig. T28A
ECG2386 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	2 Min	600 Min	±20 Max*	6	4.5 Max	1.2 Max	1800 Max	150 Max	
ECG2384 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	1.8 Min	800 Min	±20 Max*	6	4 Max	1.5 Max	3500 Max	125 Max	
ECG2900 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	60 Min	±20 Max*	12	4.5 Max	.2 Max	800 Max	75 Max	TO-220 Fig. T41 
ECG2389 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	8 Min	60 Min	±30 Max*	35	4 Max	.045 Max	2000 Max	125 Max	
ECG2395 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	17 Min	60 Min	±30 Max*	50	4 Max	.028 Max	2000 Max	150 Max	
ECG2382 ▲ (Compl to ECG2383)	MOSFET, N-Ch, Enhancement Hi Speed Switch	1.5 Min	100 Min	±20 Max*	8	4 Max	.5 Max	750 Max	75 Max	
ECG2383 ▲ (Compl to ECG2382)	MOSFET, P-Ch, Enhancement Hi Speed Switch	2 Min	100 Min	±20 Max*	8	4.5 Max	.4 Max	1200 Max	75 Max	
ECG56 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	100 Min	±20 Max*	12	4.5 Max	.18 Max	1200 Max	75 Max	
ECG2371 ▲	MOSFET, P-Ch, Enhancement Hi Speed Switch	6 Min	100 Min	±20 max*	19	4 Max	.2 Max	1400 Typ	150 Max	
ECG2396 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	12 Min	100 Min	±30 Max*	30	4 Max	.057 Max	2000 Max	150 Max	
ECG2372 ▲	MOSFET, P-Ch, Enhancement Hi Speed Switch	1 Min	200 Min	±20 Max*	3.5	4 Max	1.5 Max	350 Typ	40 Max	
ECG2373 ▲	MOSFET P-Ch Enhancement Hi Speed Switch	4 Min	200 Min	±20 max*	11	4 Max	.5 Max	1200 Typ	125 Max	

\* Warning - Exceeding BV<sub>GS</sub> maximum will result in permanent damage to the gate region oxide layer.  
▲ Refer to MOSFET Handling Precautions - Page 1-34

Package Outlines - See Page 1-91

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